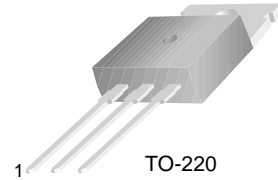


TIP105/106/107

Monolithic Construction With Built In Base-Emitter Shunt Resistors

- High DC Current Gain : $h_{FE}=1000$ @ $V_{CE}=-4V$, $I_C = -3A$ (Min.)
- Collector-Emitter Sustaining Voltage
- Low Collector-Emitter Saturation Voltage
- Industrial Use
- Complementary to TIP100/101/102

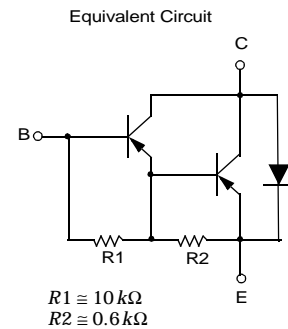


TO-220
1.Base 2.Collector 3.Emmitter

PNP Epitaxial Silicon Darlington Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CBO}	Collector-Base Voltage	: TIP105	- 60	V
		: TIP106	- 80	V
		: TIP107	- 100	V
V_{CEO}	Collector-Emitter Voltage	: TIP105	- 60	V
		: TIP106	- 80	V
		: TIP107	- 100	V
V_{EBO}	Emitter-Base Voltage	- 5	V	
I_C	Collector Current (DC)	- 8	A	
I_{CP}	Collector Current (Pulse)	- 15	A	
I_B	Base Current (DC)	- 1	A	
P_C	Collector Dissipation ($T_a=25^\circ\text{C}$)	2	W	
	Collector Dissipation ($T_C=25^\circ\text{C}$)	80	W	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$	



Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = -30\text{mA}$, $I_B = 0$: TIP105	-60	V
			: TIP106	-80	V
			: TIP107	-100	V
I_{CEO}	Collector Cut-off Current	$V_{CE} = -30\text{V}$, $I_B = 0$ $V_{CE} = -40\text{V}$, $I_B = 0$ $V_{CE} = -50\text{V}$, $I_B = 0$: TIP105	-50	μA
			: TIP106	-50	μA
			: TIP107	-50	μA
I_{CBO}	Collector Cut-off Current	$V_{CB} = -60\text{V}$, $I_E = 0$ $V_{CB} = -80\text{V}$, $I_E = 0$ $V_{CB} = -100\text{V}$, $I_E = 0$: TIP105	-50	μA
			: TIP106	-50	μA
			: TIP107	-50	μA
I_{EBO}	Emitter Cut-off Current	$V_{BE} = -5\text{V}$, $I_C = 0$		-2	mA
h_{FE}	DC Current Gain	$V_{CE} = -4\text{V}$, $I_C = -3\text{A}$ $V_{CE} = -4\text{V}$, $I_C = -8\text{A}$	1000 200	20000	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}$, $I_B = -6\text{mA}$ $I_C = -8\text{A}$, $I_B = -80\text{mA}$		-2	V
				-2.5	V
$V_{BE(on)}$	Base-Emitter ON Voltage	$V_{CE} = -4\text{V}$, $I_C = -8\text{A}$		-2.8	V
C_{ob}	Output Capacitance	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 0.1\text{MHz}$		300	pF

Typical Characteristics

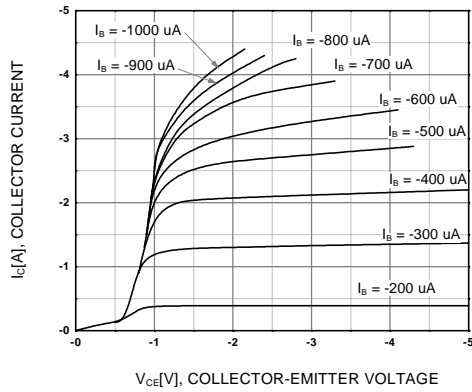


Figure 1. Static Characteristic

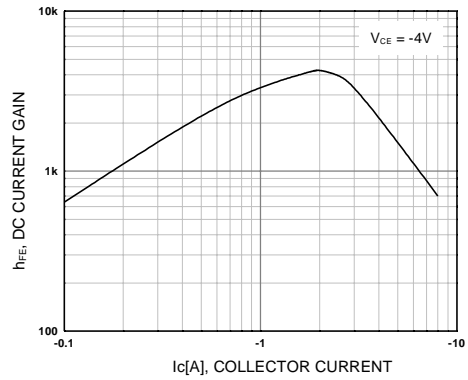


Figure 2. DC current Gain

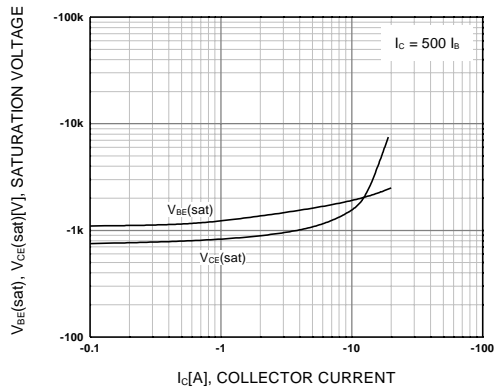


Figure 3. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage

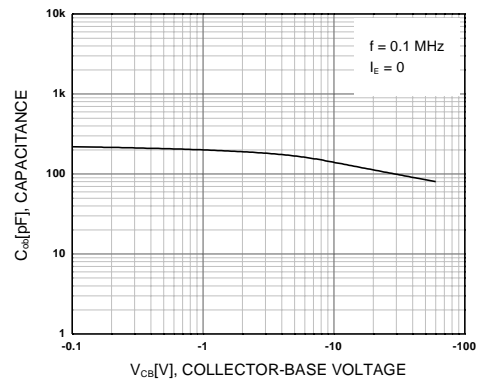


Figure 4. Collector Output Capacitance

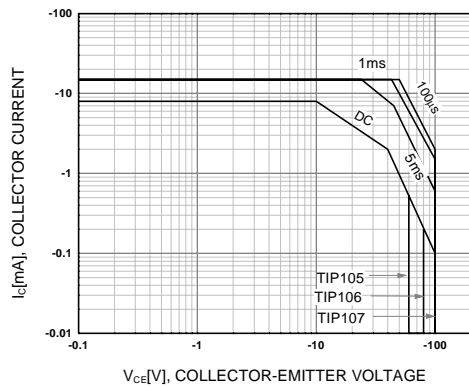


Figure 5. Safe Operating Area

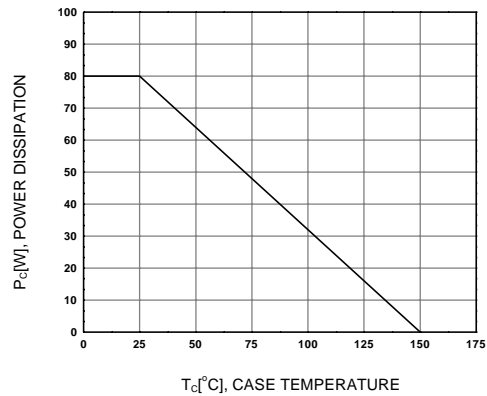
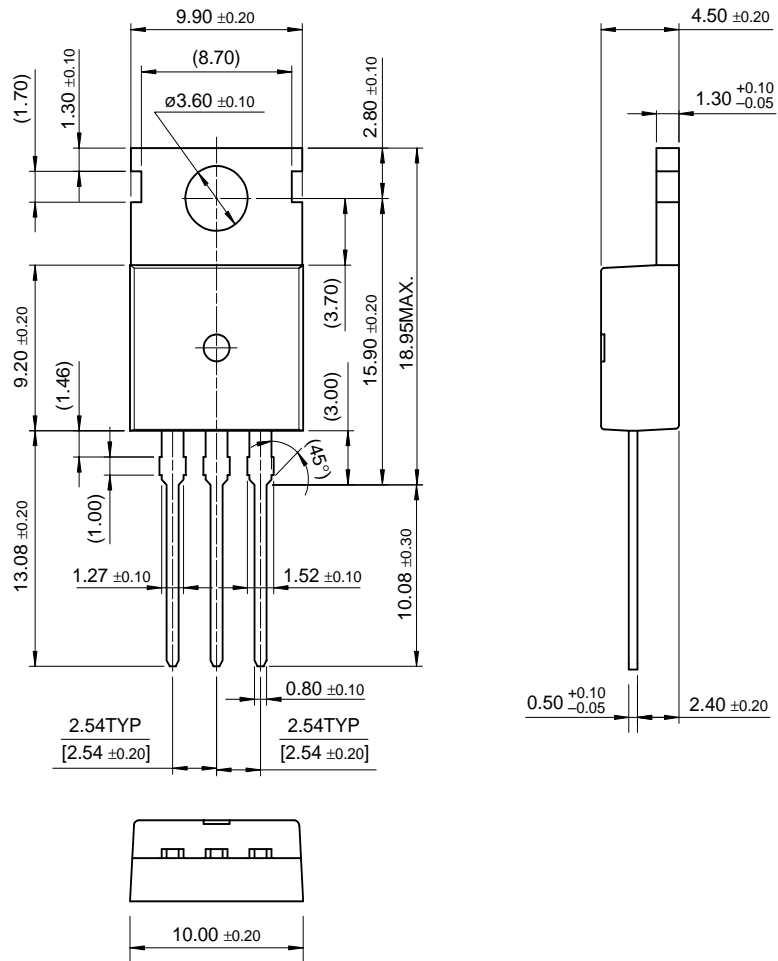


Figure 6. Power Derating

Package Dimensions

TO-220

TIP105/106/107



Dimensions in Millimeters

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